

IGBT Module

SK75GB12T4 T

Target Data

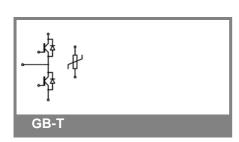
Features

- One screw mounting module
- Trench4 IGBT technology
- CAL4 technology FWD
- Integrated NTC temperature sensor

Typical Applications*

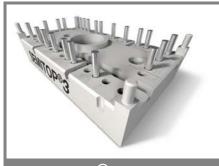
Remarks

• V_{CE,sat} , V_F = chip level value



Absolute Maximum Ratings T _s = 25 °C, unless otherwise specified						
Symbol	Conditions		Values	Units		
IGBT				<u>.</u>		
V_{CES}	T _j = 25 °C		1200	V		
I _C	$T_{j} = 175 ^{\circ}\text{C}$ $T_{s} = 25$	°C	80	Α		
	T _s = 70	°C	65	Α		
I _{CRM}	I _{CRM} = 3 x I _{Cnom}		225	Α		
V_{GES}			± 20	V		
t _{psc}	V_{CC} = 800 V; $V_{GE} \le 15$ V; V_{j} = 150 Vces < 1200 V) °C	10	μs		
Inverse D	Piode					
I _F	$T_{j} = 175 ^{\circ}\text{C}$ $T_{s} = 25$		70	Α		
	T _s = 70	°C	55	Α		
I _{FRM}	I _{FRM} = 3 x I _{Fnom}		225	Α		
I _{FSM}	$t_p = 10 \text{ ms}$; half sine wave $T_j = 150$	°C	425	Α		
Module						
$I_{t(RMS)}$				Α		
T_{vj}			-40 +175	°C		
T _{stg}			-40 +125	°C		
V_{isol}	AC, 1 min.		2500	V		

Characteristics T _s = 25 °C, unless otherwise specified						pecified
Symbol	Conditions		min.	typ.	max.	Units
IGBT						
$V_{GE(th)}$	$V_{GE} = V_{CE}$, $I_C = 3 \text{ mA}$		5	5,8	6,5	V
I _{CES}	$V_{GE} = 0 V, V_{CE} = V_{CES}$	T _j = 25 °C			0,01	mA
		T _j = 125 °C				mA
I _{GES}	V _{CE} = 0 V, V _{GE} = 20 V	$T_j = 125 ^{\circ}\text{C}$ $T_j = 25 ^{\circ}\text{C}$			600	nA
		T _j = 125 °C				nA
V_{CE0}		T _j = 25 °C		1,1	1,3	V
		T _j = 150 °C		1	1,2	V
r _{CE}	V _{GE} = 15 V	T _j = 25°C		10		mΩ
		T _j = 150°C		16		mΩ
V _{CE(sat)}	I _{Cnom} = 75 A, V _{GE} = 15 V	T _j = 25°C _{chiplev} .		1,85	2,05	V
		$T_j = 150^{\circ}C_{chiplev}$		2,25	2,45	V
C _{ies}				4,4		nF
C _{oes}	$V_{CE} = 25, V_{GE} = 0 V$	f = 1 MHz		0,29		nF
C _{res}				0,235		nF
Q_G	V _{GE} =-7V+15V			570		nC
R _{Gint}	T _j = 25 °C			10		Ω
t _{d(on)}				63		ns
t.	$R_{Gon} = 24 \Omega$	$V_{CC} = 600V$		65		ns
E _{on}	di/dt = 1360 A/μs	I _C = 75A		13,6		mJ
^I d(off)	$R_{Goff} = 24 \Omega$	$T_j = 150 ^{\circ}\text{C}$		521		ns
t _f		V _{GE} = -7/+15V		80		ns
E _{off}				8,2		mJ
$R_{th(j-s)}$	per IGBT			0,74		K/W



SEMITOP® 3

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Remarks

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Characteristics								
Symbol	Conditions	ĺ	min.	typ.	max.	Units		
Inverse Diode								
$V_F = V_{EC}$	I_{Fnom} = 75 A; V_{GE} = 0 V	$T_j = 25 ^{\circ}C_{\text{chiplev.}}$		2,1	2,5	V		
		T _j = 150 °C _{chiplev.}		2,4	2,5	V		
V_{F0}		T _j = 25 °C		1,3	1,5	V		
		T _j = 150 °C		0,9	1,1	V		
r _F		T _j = 25 °C		12	13,3	mΩ		
		T _j = 150 °C		16	17,3	mΩ		
I _{RRM}	I _F = 75 A	T _j = 150 °C		41		Α		
Q_{rr}	di/dt = 1360 A/µs			10,6		μC		
E _{rr}	V _{CC} = 600V			3,39		mJ		
R _{th(j-s)D}	per diode			0,97		K/W		
M_s	to heat sink				2,5	Nm		
w				30		g		
Temperature sensor								
R ₁₀₀	T _s =100°C (R ₂₅ =5kΩ)			493±5%		Ω		

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.

